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# Photoelectric Characteristics of Nano TiO<sub>2</sub> Film Prepared By Spraying Pyrolysis Method

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Review Article

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#### **Abstract**

The nanocrystalline  $\rm TiO_2$  (nc  $\rm TiO_2$ ) film was prepared by spraying pyrolysis method. Starting material for the synthesis was TiCl4 . Phase compositions and crystalline sizes were examined by pattern of XRD, and surface morphology of the thin film was analyzed by SEM and AFM. Optical characteristics were examined by UV – Vis and luminescent spectra (PL). Electric characteristics were examined by measuring resistance changing of films versus temperature. The experimental data showed that the forming films had nanostructure and typical photoelectric characteristics of nano  $\rm TiO_2$  material which is similar to the ones prepared by other preparing methods. IF compared to others, this preparing method has such as simple equipments, inexpensive and available materials; so it is suitable for mass production.

**Keywords:** Nano TiO<sub>2</sub> film; Spraying Pyrolysis Method.

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#### **Introduction**

Nano titanium oxide has a lot of applications in real life. It is used to make dye in industry to produce paint, plastic, paper and food products. TiO<sub>2</sub> has been even covered on interior furniture to create reflected light effects which increase their beauty, etc. Together with development of nano material technology, at present, there are important applications of nano (nc)  $\text{TiO}_2$  including photocatalysis, solar cells, photon and photoelectron devices, etc. With oxidation potential is 3.2 eV, under effect of ultraviolet light (UV), nc TiO<sub>2</sub> can decompose very strong toxic wastes in environment.

 $\rm TiO_2$  was used as an insulating gate on the field effect transistor (FET) [\[15\],](#page-5-0) to make detectors for measuring nuclear radiations [\[2\]](#page-5-1), and to make luminescence devices [\[4\].](#page-5-2) When doping more appropriate impurities, it will create energy levels of Ea located in the bandgap. If electrons simultaneously jump from excited levels to elementary energy levels, the material shall generate desired

radiations. The change of color windows act based on this principle. The impurities energy levels can be controlled by electric field; therefore, we have color changing instantaneously depending on the control of the electric field  $[10, 20]$  $[10, 20]$ . TiO<sub>2</sub> was also used to make anti reflexing layers help enhancement of efficiency of photosemiconductor amplifiers (laser) GaInAs/AlGaInAs [\[12\]](#page-5-5). Because  $TiO<sub>2</sub>$  has very large refractive index, fiber optic cables or optic windows covered this material, which acts based on continuous reflection principle, will produce total reflect, which will minimize the loss of light (sign).

There have been different methods used to prepare nano materials and nano films from relatively simple to rather complex including physics methods (Physical vapor deposition – PVD), chemical methods (Chemical vapor deposition – CVD) and many others such as physics and chemical combined method or combined different methods.

Spraying pyrolysis method (SP) is one of the most simple and economic methods to prepare oxide metals. Using nano TiO<sub>2</sub> films prepared by SP method and using inexpensive materials can enhance applied ability of this material [\[1\]](#page-5-6). Besides the simplicity of the method, low cost with a minimum amount of waste, SP process even permits to prepare cover layers with large areas and easily apply for industrial manufacture [\[8\]](#page-5-7). This is remarkable advantage of SP method compared to other methods.

SP method has been used by many authors to prepare nano  $TiO<sub>2</sub>$ films including single atom films and polyatomic films from different starting salts. Actually, the authors [\[18\]](#page-5-8) sprayed pyrolysis liquid mixture of titanium and niobium peroxo-hydroxo on quartz substrate to prepare oxygen sensitive sensor. Another authors [\[5\]](#page-5-9) prepared  $\text{TiO}_2$  films and carbon doped  $\text{TiO}_2$  powder using starting material was titanium-tetraisopropoxide, the obtained films have anatase single phase structure, the average size of crystalline particles was  $\sim$  160 nm. Additionally, the authors [\[1\]](#page-5-6) prepared

 $\text{TiO}_2$  films on glass substrate using titanium (IV) isobutoxide [Ti  $((CH<sub>3</sub>)<sub>2</sub>CHCH<sub>2</sub>O)<sub>4</sub>]$  as starting material. Also, the authors [\[19\]](#page-5-10) prepared  $\text{TiO}_2$  films on glass substrate using starting material of  $C_{10}H_{14}O_5Ti$ , the obtained films have the crystalline particle size from 30nm to 50nm. The authors  $[17]$  prepared  $TiO<sub>2</sub>$  films by starting materials of TiCl<sub>3</sub> solution. The authors [\[4\]](#page-5-2) prepared  $TiO<sub>2</sub>$  films by using titanium diisopropoxide as starting material, the average size of crystalline particles was  $\sim$  210nm.

#### **Experiments**

#### **Materials**

TiCl4 was prepared into solution with concentrations ranging from 0.025 to 0.15mol/dm<sup>3</sup> (M). The solution was sprayed with atmosphere-pressing pressure 1.5 at. Substrates were made by optical glass with thickness of 1.2mm. Substrate temperatures were studied ranged from 340°C to 460°C.

#### **Apparatus**

X-ray diffraction patterns (XRD) of nanocrystalline  $\text{TiO}_2$  films were measured by a D8-AVANCE BRUKER X-ray diffractometer using Cu K $\alpha$  radiation (k = 0.1542nm) with 0.02°/sec scan rate. Field effect scanning electron micrographs (FESEM) were taken with a FESEM HITACHI S4800 field effect scanning electron microscope. Atom force micrographs were taken with a Multimode-VEECO-USA atom force microscope. UV-Vis absorption spectra were measured by a Shimadzu UV-Vis 2540 absorption spectrometer. Luminesce spectra were measured by a FL 3-22 Jobin – Yvon – Spec., USA.

#### Apparatus for preparing nano TiO<sub>2</sub> by spraying pyrolysis **method**

This apparatus are self-prepared. Scheme of nano  $TiO_2$  film preparing system by spraying pyrolysis deposition method was showed in Figure 1. Temperature controlling system used digital technology of OMRON company with degree of displaying accuracy of 1°C. Steam pressure was controlled by two compressed

valves of UniD800 (Taiwan). Spraying frequency was controlled by electronic IC system which may control all of pulse to alter not only spraying time but also pausing time.

#### **Results and Discussion**

# Structure and morphology of nano TiO<sub>2</sub> films

The crystalline phase of ellipsoidal  $\rm TiO_2$  was characterized by Xray diffractometer. Figure 2 shows the film XRD pattern deposited from spraying pyrolysis deposition method at 380°C with solution concentrate of  $TiCl<sub>4</sub> = 0.03 M$ . The XRD pattern shows that Bragg reflections were very clear at typical diffraction angles  $2\theta$  = 25.4°, 38.8°, 48.0° and 55.0° corresponding to crystalline planes: (101), (112), (200) and (211), they were the same as results of the authors [\[11\]](#page-5-12). All of the films had single phase anatase structure.

Figure 3 shows the XRD patterns of the films prepared at different substrate temperatures at the same experimental condition. The XRD patterns showed that at the studying temperature range of 340 – 460°C, all of the formed films had single phase anatase structure.

The surface morphologies of the film deposited at 450°C are shown in Figure. 3 and 4. From the profiles, it can be observed that the film is porous nanostructure with the average grain size of about 20nm. This relates to evaporation process of solvent and semi-finished product in the pyrolysis process from starting material. Image of Scanning electron micrograph (SEM) of the typical pattern prepared by solution concentrate 0.1 M and at temperature of 450°C is shown in Figure. 4 and its atomic force micrograph (AFM) are shown in Figure 5.

The SEM shows the particles are distributed relatively homogeneously and mesoporously. This result agrees with the SEM of nano  $\text{TiO}_2$  film of authors prepared by different methods [\[6,](#page-5-13) [7\].](#page-5-14)

The AFM image shows that size of crystalline particles obtained in this work relatively uniform at the range  $\sim 10-15$  nm, roughness of film was about 100nm, there were a lot of holes inside





Figure 2. The XRD pattern of TiO<sub>2</sub> film prepared from spraying pyrolysis deposition method at 380°C.



**Figure 3. The XRD patterns of TiO<sup>2</sup> films prepared from spraying pyrolysis deposition method at different substrate temperatures**



Figure 4. SEM image of nano TiO<sub>2</sub> film deposited from spraying pyrolysis deposition method at substrate temperature of **450**°**C**



Figure 5. AFM image of nano TiO<sub>2</sub> film deposited from spraying pyrolysis deposition method at temperature of 450°C.



the film. Combined with SEM image, it can be seen that sizes of holes varied on a large scale – in range from  $\sim$  20 nm to  $\sim$  200 nm. The formed films had a very porous structure, so they may have high efficiency on applications of photocatalysis and photoelectrochemical dye sensitized solar cells.

# **Optical characteristics of nano TiO**<sub>2</sub> films

Figure 6 shows the absorption spectrum of nano crystalline TiO<sub>2</sub> films prepared at substrate temperature of 450°C and solution concentration of 0.1M. Absorption of the films was a function of light wavelength, it slowly increased according to decreasing of wavelength in visible light range, but in ultra violet range absorption coefficient increased very fast corresponding with level transitions band – band of electrons from valence band to conduction band of nano  $TiO<sub>2</sub>$ . The shape of absorption spectrum obtained here was the same as that of the authors prepared from TiCl<sub>3</sub> by the same SP method [\[17\]](#page-5-11), or from TiCl<sub>4</sub> and Ti(SO<sub> $\psi$ 2</sub> by other methods  $[3, 23, 24]$  $[3, 23, 24]$  $[3, 23, 24]$  $[3, 23, 24]$ , or from commercial nano  $\text{TiO}_2$  powder by doctor blade method [\[22\],](#page-5-18) or of nano TiO<sub>2</sub> particles prepared by hydrolysis method TiCl $[14]$ .

Adsorption edge was determined by linear extrapolation of absorption coefficient  $\alpha$  in absorption range to value 0 as well as the authors made [\[16\].](#page-5-20) Obtained result was adsorption edge at 370 nm, corresponding with photon energy at 3.35 eV.

From absorption spectrum, we can calculate bandgap size from expression for fundamental adsorption coefficient:

$$
\alpha(h\gamma) = A[h\gamma - (Eg \pm h\gamma_{\rho})]^2 \text{ --- } (1)
$$

Where hγ denotes energy of photon, Eg is bandgap energy of semiconductor, hγf denotes energy of phonon, A is constant.

The authors [\[6](#page-5-13), [9,](#page-5-21) [17,](#page-5-11) [19.](#page-5-10) [23\]](#page-5-16) calculated bandgap size for nano  $\rm TiO_2$  according to Tauc model in the range of high absorption coefficient [\[9\]](#page-5-21) by expression:

$$
\alpha = \frac{A(h\gamma - E_g)^{n/2}}{h\gamma} \quad \text{...... (2)}
$$

A is constant which is not dependent on energy of photon, but according to the authors  $[6]$  then A is absorption coefficient which is dependent on energy of photon for the case of nano TiO<sub>2</sub>; n = 1 for allowed direct level transitions, n = 4 for allowed indirect level transitions,  $n = 3$  for forbidden indirect optical level transitions.

Graph expresses  $(\alpha h \gamma)^{1/2}$  that is calculated according to absorption spectrum of nano  $TiO<sub>2</sub>$  film in Figure 7 on photon energy of incident light was showed on figure 6. Bandgap size  $\sim$  3.35 eV was obtained by extrapolating linearly at the absorption range with high photon energy to value  $\alpha = 0$ . This result was in the value range of other authors [\[3](#page-5-15), [23](#page-5-16), [24\]](#page-5-17).

Obtained  $E_{\rm g}$  value was larger than that of anatase  $\rm TiO_2$  bulk (3.2) eV). The cause may not be by nonstoichiomatric composition of nano  $TiO<sub>2</sub>$  film, since the nonstoichiomatric composition leads to decrease in bandgap size. According to [\[21\]](#page-5-22), a nonstoichiometry only leads to creating oxygen vacancies (Ti3+) acting as trap levels

in  $TiO<sub>2</sub>$  layers but does not lead to increasing in bandgap size. This occurs similarly to doped semiconductor. All of the authors reckoned that the increase of bandgap size for nano  $\rm TiO_2$  prepared by different methods with different starting materials was due to quantization of size [\[14,](#page-5-19) [16,](#page-5-20) [22,](#page-5-18) [23\]](#page-5-16). The obtained value was in the value range of other authors for nano  $\text{TiO}_2$  films prepared by SP method from different starting materials:  $E<sub>g</sub> = 3.31 - 3.36$ eV from Titanyl acetylacetonate (TiAcAc) [\[19\]](#page-5-10). Direct bandgap size  $E_g = 3.1$  eV from TiCl<sub>3</sub> [\[17\].](#page-5-11)  $E_g = 2.99$ ; 3.30 và 3.32 eV from solution of ethanol titanium diisopropoxide, corresponding to substrate temperatures were 250, 400 and 500°C [\[3\]](#page-5-15).  $E_g \sim 3.8 \text{ eV}$ from titanium (IV) isobutoxide [\[1\].](#page-5-6) Indirect optical bandgap size  $E<sub>g</sub>$  = 3.39 – 3.42 eV and direct optical bandgap size  $E<sub>g</sub>$  = 3.67 –  $3.72$  eV [\[9\].](#page-5-21)

Figure 8 shows luminescent spectrum of nano  $TiO_2$  film was excited at wavelength of 330nm. Luminescent spectrum had maximum peak at wavelength of 394.5nm.

In nano TiO<sub>2</sub> material system, luminescent level transitions were band–band level transitions, band–dopant and exiton recombinations. The peaks on luminescent spectrum corresponded with optical level transitions. Maximum of luminescent spectrum stretched in large range may be due to the overlapping spectrum peaks. Luminescent spectrum of anatase nano  $\mathrm{TiO}_2$  patterns was thought to belong to exiton traps, oxygen vacant and surface states [\[13\]](#page-5-23).

UV-Vis adsorption and luminescent spectra of nano  $TiO_2$  film here had the same shape as nano  $\text{TiO}_2$  films prepared by other methods [\[16,](#page-5-20) [23,](#page-5-16) [24\].](#page-5-17)

# Electric characteristics of nano TiO<sub>2</sub> films

To study electric characteristics of obtained films, the change of film resistance versus temperature was measured. Studying -temperature range is from room temperature to 450°C. At room temperature, the film was almost insulated. From about 150°C, the film started electric-conducting and then its resistance gradually decreased with temperature increase. This is a typical rule of semiconductor materials. This change rule is shown in Figure 9. From the graph of  $ln(1/R)$  versus temperature inverse, here R is resistance of film, we can determine two energy levels:

– At high temperature range, conductivity of film increased due to only heat excitations to jump electrons from valence band to conduction band – this is a range relating to intrinsic conductivity of semiconductor – has value of $\sim$ 3.32 eV, corresponding with bandgap energy of nano TiO<sub>2</sub>. This result was relevant to the calculated results  $E_g$  from UV–Vis absorption spectrum measurement ( $\sim$  3.35 eV).

– At low temperature range, conductivity of film was mainly because carriers were created from dopants ionized – this was a range of conductivity as dopants for extrinsic semiconductor – had value of  $\sim$  0.69 eV, corresponding with dopant level, it may be due to unexpected dopants. This was deep level so it had large carrier catching cross-section. These deep centres relate to luminescent process of TiO<sub>2</sub>, because deep centres usually act as recombinations or effective traps and control life-time of carriers.

Figure 6. UV-Vis absorption spectra of nano TiO<sub>2</sub> film prepared at 450°C.



**Figure 7.**  $(\alpha h v)^{1/2}$  as a function of  $\mu v$  for the TiO<sub>2</sub> film calculated according to absorption spectra of nano TiO<sub>2</sub> in figure 6.



Figure 8. Luminescent spectrum of nano TiO<sub>2</sub> film excited at wavelength 330nm.



Figure 9. The dependence of resistance of nano TiO<sub>2</sub> film on temperature.



# **Conclusion**

Nanocrytalline  $TiO<sub>2</sub>$  films were prepared by spraying pyrolysis method. Experimental results show that at substrate temperature ranging from 340°C to 460°C with solution concentration from 0.025 to 0.15M, all of them gave  $TiO_2$  films condensed on glass substrate. These were anatase single phase, nanocrytalline TiO2 films with high crystalline quality and cleanliness, equivalent to other expensive prepared methods include comparison with commercial products. The films had mesoporous structure with average sizes of crystalline particles were at range 7–10nm which were lightly dependent on starting-solution concentration and prepared temperature. This method gave nano  $\text{TiO}_2$  films with small particle size and high stability in comparison with other methods.

Characteristic studying results showed that the obtained nano TiO<sub>2</sub> films sufficiently exposed typical photoelectric characteristics of TiO<sub>2</sub> semiconductor material. Characteristic parameters such as absorption spectrum, luminescent spectrum, bandgap size were suitable and equivalent to data of other authors.

Therefore spraying pyrolysis method with simple equipments, used inexpensive and available materials enables to prepare nano  $TiO<sub>2</sub>$  films with high quality to meet demands of fundamental and applied researches. This method is able to apply in industrial production.

#### **References**

- <span id="page-5-6"></span>[1]. Abou-Helal MO, Seeber WT (2002) "Preparation of  $TiO<sub>2</sub>$  thin films by spray pyrolysis to be used as a photocatalyst". App. Surf. Sci 195: 53 – 6.
- <span id="page-5-1"></span>[2]. Arshak K, Corcoran J, Korostynska O (2005) "Gamma radiation sensing properties of  $TiO<sub>2</sub>$ , ZnO, CuO and CdO thick film pn-junctions". Sensors and Actuators A 123: 194 – 198.
- <span id="page-5-15"></span>[3]. Castillo N, Olguin D, Conde-Gallardo A (2004) "Structural and morphological properties of TiO<sup>2</sup> thin films prepared by spray pyrolysis". Rev. Mex. Fis 50(4): 382 – 387.
- <span id="page-5-2"></span>[4]. Conde-Gallardo A, García-Rocha M, Hernández-Calderón I, Palomino-Merino R (2001) "Photoluminescence properties of the Eu<sup>3+</sup> activator ion in the TiO<sub>2</sub> host matrix". Appl. Phys. Lett 78:  $3436 - 3438$ .
- <span id="page-5-9"></span>[5]. Cristina S. Enache, Joop Schoonman, Roel van de Krol (2006) "Properties of Carbon-doped TiO<sub>2</sub> (Anatase) Photo-Electrodes". Mater. Res. Soc. Symp. Proc 885: 0885-A10.
- <span id="page-5-13"></span>[6]. Elena Vigil, José A Ayllón, Ana M Peiró, Rafael Rodríguez-Clemente, Xavier Domènech, et al. (2001) "TiO<sub>2</sub> Layers Grown from Flowing Precursor Solutions Using Microwave Heating". Langmuir 17: 891 – 896.
- <span id="page-5-14"></span>[7]. Garzella C, Comini E, Tempesti E, Frigeri C, Sberveglieri G (2000) "TiO2 thin films by a novel sol-gel processing for gas sensor applications". Sensors and Actuators B 68: 189 – 196.
- <span id="page-5-7"></span>[8]. Gümüş C, Ozkendir OM, Kavak, Ufuktepe Y (2006) "Structural and optical properties of zinc oxide thin films prepared by spray pyrolysis method". J. Optoel. and Adv. Mater. 8(1): 299 – 303.
- <span id="page-5-21"></span>[9]. Hasan MM, Haseeb ASMA, Saidur R, and Masjuki HH (2008) "Effects of Annealing Treatment on Optical Thin Films Properties of Anatase TiO<sub>2</sub>", Proceeding world academy of science, engineering and technology 30: 221 – 225.
- <span id="page-5-3"></span>[10]. <http://kuroppe.tagen.tohoku.ac.jp/~ecd/museum-j.htm>
- <span id="page-5-12"></span>[11]. Jae P Lee, Mi H Park, Taek-Mo Chung, Yunsoo Kim, Sung Myung M (2004) "Atomic Layer Deposition of TiO<sub>2</sub> Thin Films from Ti $(\mathrm{OiPr})_{2}(\mathrm{dmae})_{2}$  and H2 O". Bull. Korean Chem. Soc 25(4): 475 – 479.
- <span id="page-5-5"></span>[12]. Madhusudan Reddy K, Gopal Reddy CV, Manorama SV (2001) "Preparation, characterization, and spectral studies on nanocrystalline anatase  $\text{TiO}_2$ . Journal of Solid State Chemistry 158: 180 – 186.
- <span id="page-5-23"></span>[13]. Lee J, Tanaka T, Uchiyama S, Tsuchiya M, Kamiya T (1997) "Broadband double-layer antireflection coatings for semiconductor laser amplifiers", Japanese Journal of Applied Physics 36(2): L52 – L54.
- <span id="page-5-19"></span>[14]. Lei Y, Zhang LD (2001) "Fabrication, characterization, and photoluminescence properties of highly ordered  $\rm TiO_2$  nanowire arrays". J. Mater. Res 16(4): 1138 – 1144.
- <span id="page-5-0"></span>[15]. Masao Katayama, Shinya Ikesaka, Jun Kuwano, Yuichi Yamamoto, Hideomi Koinuma, et al. (2006) "Field-effect transistor based on atomically flat rutile TiO2 ". Appl. Phys. Lett 89(24): 242103-242103.
- <span id="page-5-20"></span>[16]. Mogyorósi K, Dékány I, Fendler JH (2003) "Preparation and Characterization of Clay Mineral Intercalated Titanium Dioxide Nanoparticles". Langmuir 19(7): 2938 – 2946.
- <span id="page-5-11"></span>[17]. More AM, Gunjakar JL, Lokhande CD (2008) "Liquefied petroleum gas (LPG) sensor properties of interconnected web-like structured sprayed TiO2 films", Sensors and Actuators B 129: 671 – 677.
- <span id="page-5-8"></span>[18]. Nickolay Golego, Studenikin SA, Michael Cocivera (2000) "Sensor Photoresponse of Thin-Film Oxides of Zinc and Titanium to Oxygen Gas". J. Elec. chem. Soc 147(4): 1592 – 1594.
- <span id="page-5-10"></span>[19]. Pravin S Shinde, Pramod S Patil, Popat N Bhosale, Chandrakant H Bhosalew (2008) "Structural, Optical, and Photoelectrochemical Properties of Sprayed  $\text{TiO}_2$  Thin Films: Effect of Precursor Concentration". J. Am. Ceram. Soc 91(4): 1266 - 1272.
- <span id="page-5-4"></span>[20]. Rachel Cinnsealach, Gerrit Boschloo, Nagaraja Rao S, Donald Fitzmaurice (1999) "Coloured electrochromic windows based on nanostructured TiO<sub>2</sub> films modified by adsorbed redox chromophores". Solar Energy Materials and Solar Cells 57(2): 107 – 125.
- <span id="page-5-22"></span>[21]. Sathyamoorthy R, Sudhagar P, Chandramohan S, and Vijayakumar KP (2007) "Photoelectrical properties of crystalline titanium dioxide thin films after thermo-annealing". Crys. Res. Tech 42(5): 498 – 503.
- <span id="page-5-18"></span>[22]. The-Vinh Nguyen, Hyun-Cheol Lee, O-Bong Yang (2006) "The effect of pre-thermal treatment of  $TiO<sub>2</sub>$  nano particles on the performance of dyesensitized solar cells". Solar Energy Materials & Solar cells 90: 967 – 981.
- <span id="page-5-16"></span>[23]. Thierry Cassagneau, Janos H Fendler, Thomas E Mallouk (2000) "Optical and Electrical Characterizations of Ultrathin Films Self-Assembled from 11-Aminoundecanoic Acid Capped  $TiO<sub>2</sub>$  Nanoparticles and Polyallylamine Hydrochloride". Langmuir 16: 241 – 246.
- <span id="page-5-17"></span>[24]. Xinming Qian, Dongqi Qin, Qing Song, Yubai Bai, Tiejin Li, et al. (2001) "Surface photovoltage spectra and photo electrochemical properties of semiconductor-sensitized nanostructured  $\text{TiO}_2$  electrodes". Thin solid films  $385(1-2): 152 - 161.$